



Average gate power dissipation ($T_j=125\text{ }^{\circ}\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25\text{ }^{\circ}\text{C}$; non-repetitive, off-state; FIG. 7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

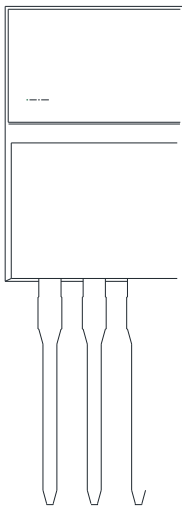
Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125\text{ }^{\circ}\text{C}$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA



ORDERING INFORMATION

J	ST	08	F	-800	BW
JieJie Microelectronics Co., Ltd.	Triacs	It(RMS):8A	F:TO-220F(Ins)	800:VDRM /VRRM ≥ 800V	BW:IGT1-3 ≤ 50mA

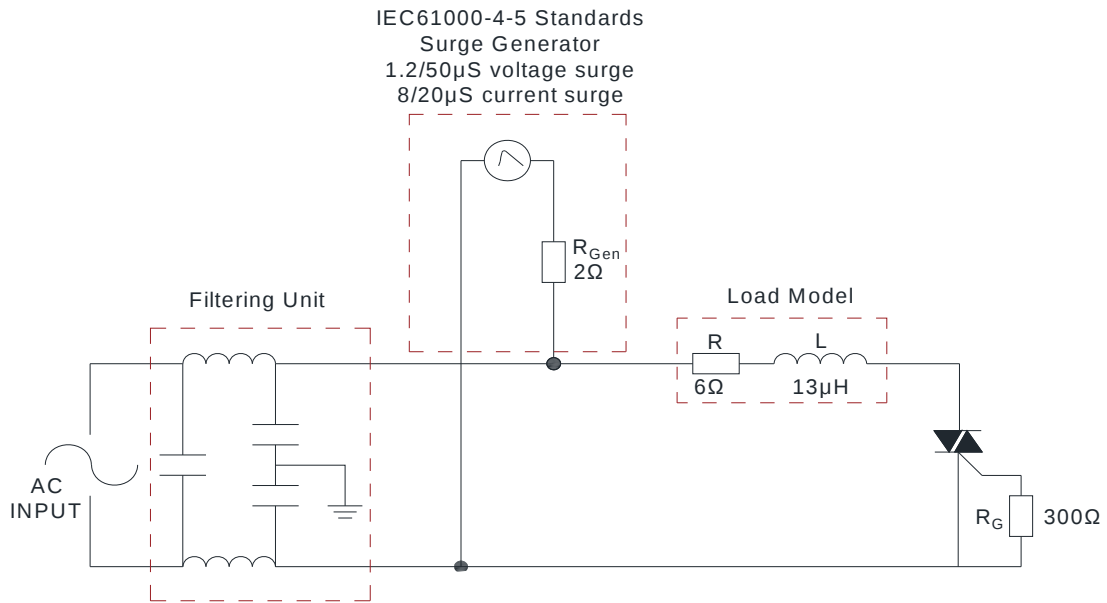
MARKING



JST08F-800BW



FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





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